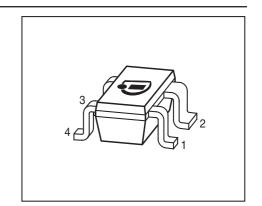


Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain broadband amplifiers at collector currents from 1 mA to 20 mA
- f_T = 8 GHz, NF_{min} = 0.9 dB at 900 MHz
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration Package						
BFP182R	RGs	1=E	2=C	3=E	4 = B	1	-	SOT143R

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I _C	35	mA
Base current	I _B	4	
Total power dissipation ¹⁾	P _{tot}	250	mW
<i>T</i> _S ≤ 69 °C			
Junction temperature	$ T_{J} $	150	°C
Storage temperature	T_{Stq}	-55 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	325	K/W

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 $^{{}^1}T_{
m S}$ is measured on the collector lead at the soldering point to the pcb

 $^{^2}$ For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	•			•	
Collector-emitter breakdown voltage	V _{(BR)CEO}	12	-	_	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-emitter cutoff current	I _{CES}	-	-	100	μΑ
$V_{CE} = 20 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB} = 10 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I _{EBO}	-	_	1	μΑ
$V_{\rm EB}$ = 1 V, $I_{\rm C}$ = 0					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, pulse measured					

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Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter Parameter $I_A = 25 ^{\circ}C$, unless	Symbol		Unit		
		min.	typ.	max.	
AC Characteristics (verified by random sampling	<u>g)</u>	1	1	1	
Transition frequency	f_{T}	6	8	-	GHz
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz					
Collector-base capacitance	C _{cb}	-	0.25	0.4	pF
$V_{\text{CB}} = 10 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,					
emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.3	_	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C _{eb}	-	0.8	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,					
collector grounded					
Minimum noise figure	<i>NF</i> _{min}				dB
$I_{\rm C}$ = 3 mA, $V_{\rm CE}$ = 6 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 900 MHz		-	0.9	-	
$I_{\rm C}$ = 3 mA, $V_{\rm CE}$ = 6 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 1.8 GHz		-	1.3	-	
Power gain, maximum stable ¹⁾	G _{ms}	-	22	-	dB
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 900 MHz					
Power gain, maximum available ²⁾	G _{ma}	-	16.5	-	dB
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 1.8 GHz					
Transducer gain	S _{21e} ²				dB
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz		-	18	-	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 1.8 GHz		-	12	-	

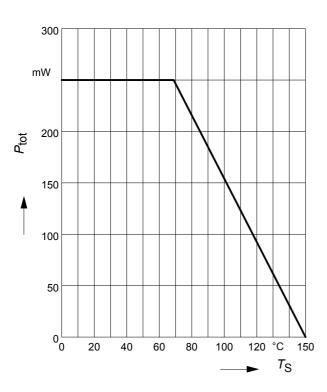
 $^{^{1}}G_{ms} = |S_{21} / S_{12}|$

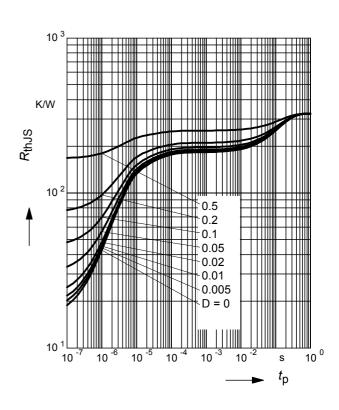
 $^{{}^{2}}G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$



Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$

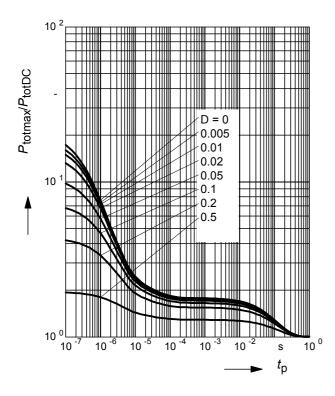
Permissible Pulse Load $R_{thJS} = f(t_p)$





Permissible Pulse Load

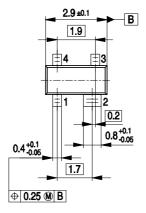
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$$

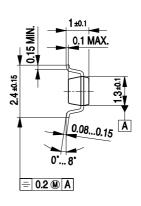




Package Outline



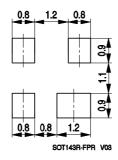




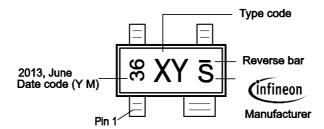
Note: Mold flash, protrusions or gate burrs of 0,2 mm max. per side are not included

SOT143R-PO V03

Foot Print

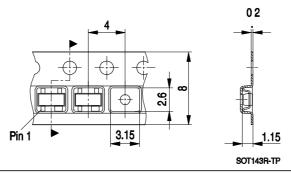


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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